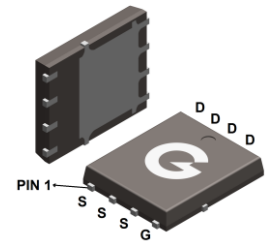
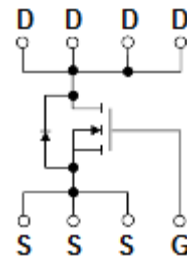


Features

- Super low gate charge
- Green device available
- Excellent C_{dv} / d_t effect decline
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

HF



Mechanical Data

- Case: PDFN5x6-8L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

PDFN5x6-8L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBL050N10T-5DL8	PDFN5x6-8L	5000 pcs / Tape & Reel	050N10T

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$) *1	I_D	59	A
Pulsed Drain Current *2	I_{DM}	236	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	35	W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	3.5	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	2.7	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_J	$-55 \sim +150$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

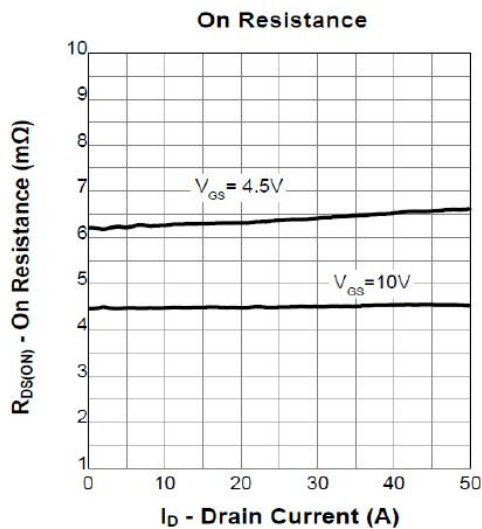
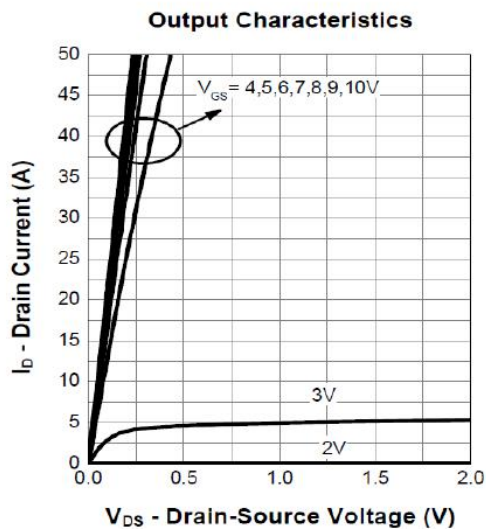
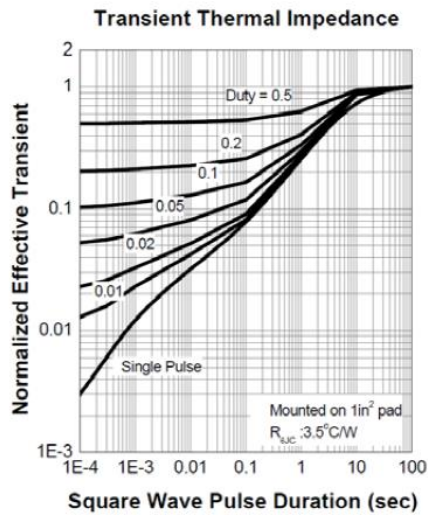
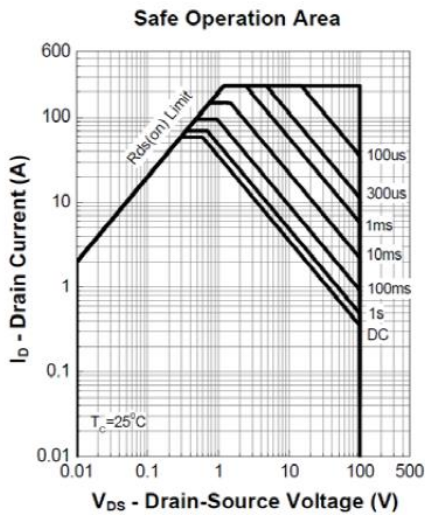
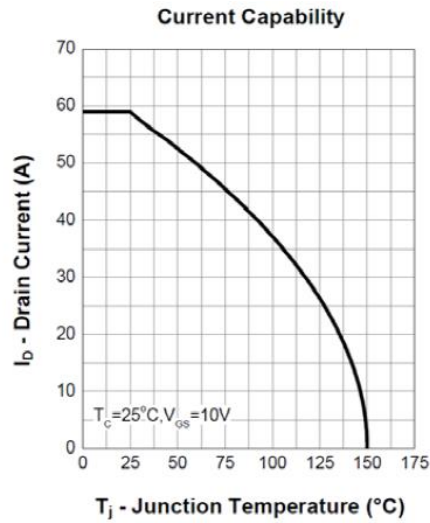
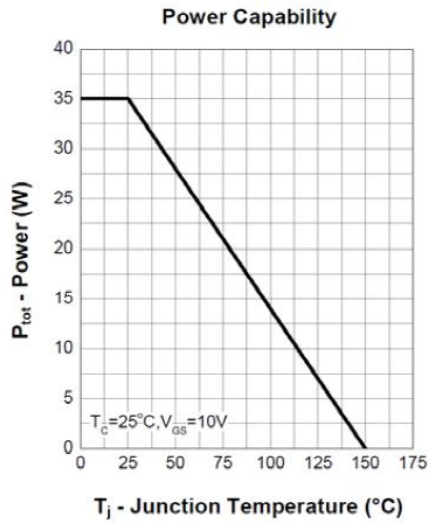
Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

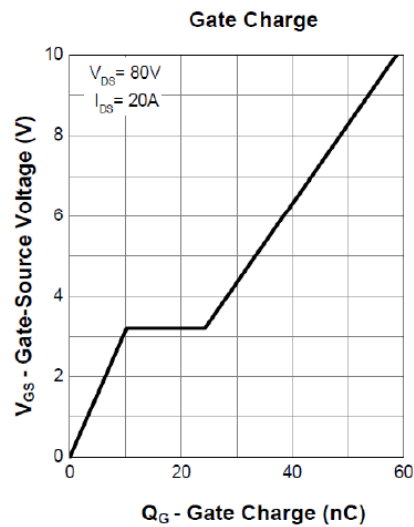
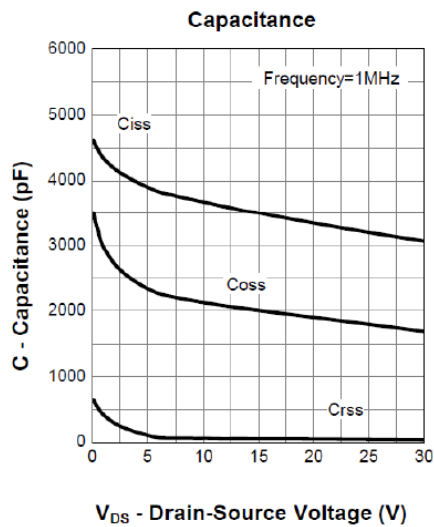
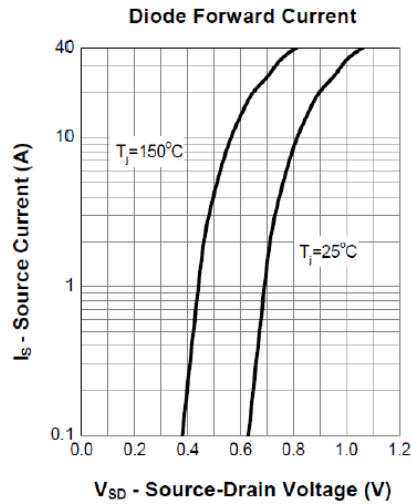
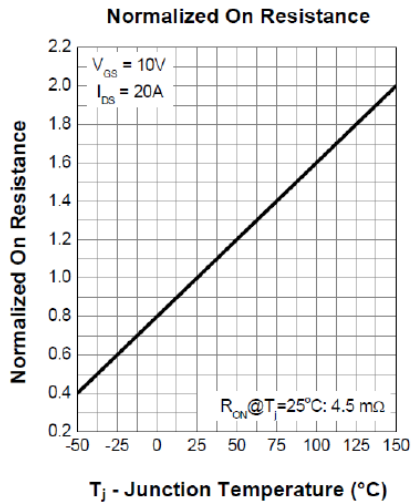
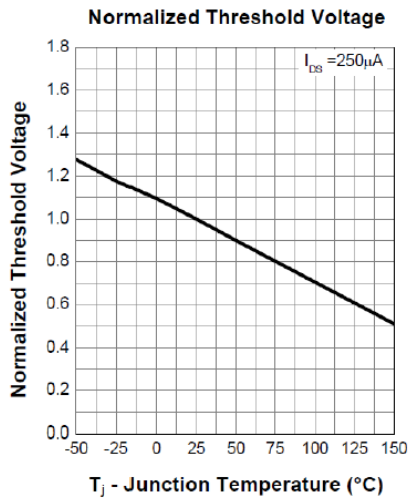
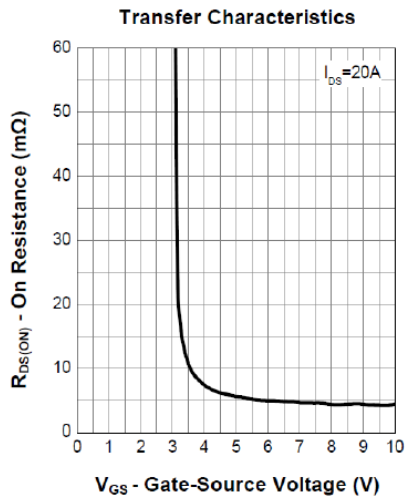
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V, T _C = 25°C	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Static Drain-Source On-resistance ^{*2}	V _{GS} = 10V, I _D = 20A	-	4.0	5.0	mΩ
		V _{GS} = 4.5V, I _D = 10A	-	5.6	8.0	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.5	2.0	2.5	V
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	-	3390	-	pF
C _{OSS}	Output Capacitance		-	1940	-	
C _{RSS}	Reverse Transfer Capacitance		-	210	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DD} =80V V _{GS} = 20V R _G = 3.3Ω V _{GS} = 10V	-	13.2	-	ns
t _r	Turn-on Rise Time		-	57.8	-	
t _{d(OFF)}	Turn-Off Delay Time		-	37.6	-	
t _f	Turn-Off Fall Time		-	63.8	-	
Q _G	Total Gate-Charge	V _{DD} = 80V V _{GS} = 10V I _D = 20A	-	58.7	-	nC
Q _{GS}	Gate to Source Charge		-	10.2	-	
Q _{GD}	Gate to Drain (Miller) Charge		-	14.1	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage ^{*2}	I _{SD} = 20A, V _{GS} = 0V	-	-	1.2	V

Notes:

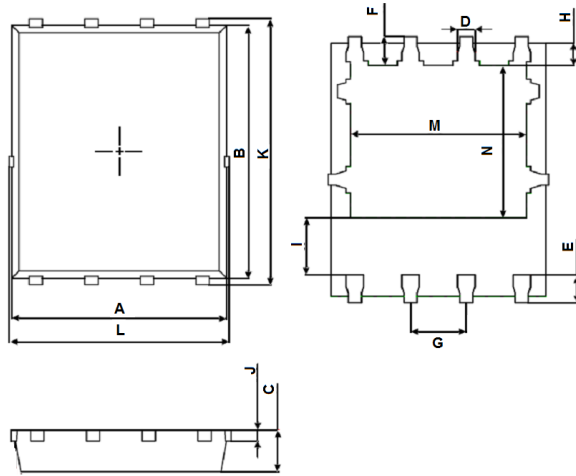
1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.5mH$
4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)





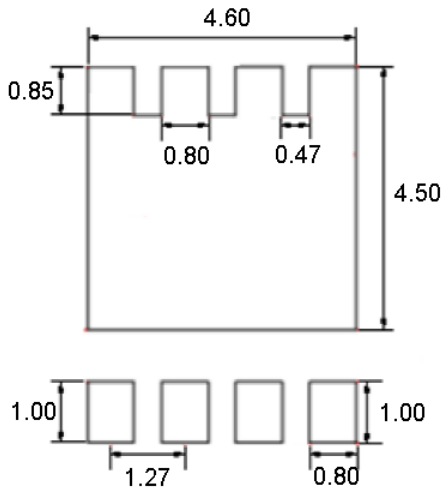
Package Outline Dimensions (Unit: mm)



PDFN5x6-8L		
Dimension	Min.	Max.
A	4.824	4.976
B	5.674	5.826
C	0.900	1.000
D	0.350	0.450
E	0.559	0.711
F	0.574	0.726
G	1.250	1.290
H	0.424	0.576
I	1.190	1.390
J	0.154	0.354
K	5.974	6.126
L	4.944	5.096
M	3.910	4.110
N	3.375	3.575

Mounting Pad Layout (Unit: mm)

PDFN5x6-8L



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